

# SSM6L36TU

○ High-Speed Switching Applications

- 1.5-V drive
- Low ON-resistance
  - Q1 N-ch:  $R_{on} = 1.52\Omega$  (max) (@ $V_{GS} = 1.5$  V)
  - $R_{on} = 1.14\Omega$  (max) (@ $V_{GS} = 1.8$  V)
  - $R_{on} = 0.85\Omega$  (max) (@ $V_{GS} = 2.5$  V)
  - $R_{on} = 0.66\Omega$  (max) (@ $V_{GS} = 4.5$  V)
  - $R_{on} = 0.63\Omega$  (max) (@ $V_{GS} = 5.0$  V)
  - Q2 P-ch:  $R_{on} = 3.60\Omega$  (max) (@ $V_{GS} = -1.5$  V)
  - $R_{on} = 2.70\Omega$  (max) (@ $V_{GS} = -1.8$  V)
  - $R_{on} = 1.60\Omega$  (max) (@ $V_{GS} = -2.8$  V)
  - $R_{on} = 1.31\Omega$  (max) (@ $V_{GS} = -4.5$  V)

**Q1 Absolute Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	20	V
Gate-source voltage		$V_{GSS}$	$\pm 10$	V
Drain current	DC	$I_D$	500	mA
	Pulse	$I_{DP}$	1000	

**Q2 Absolute Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-20	V
Gate-source voltage		$V_{GSS}$	$\pm 8$	V
Drain current	DC	$I_D$	-330	mA
	Pulse	$I_{DP}$	-660	

**Absolute Maximum Ratings (Ta = 25 °C) (Common to the Q1, Q2)**

Characteristic	Symbol	Rating	Unit
Drain power dissipation	$P_D$ (Note 1)	500	mW
Channel temperature	$T_{ch}$	150	°C
Storage temperature range	$T_{stg}$	-55 to 150	°C

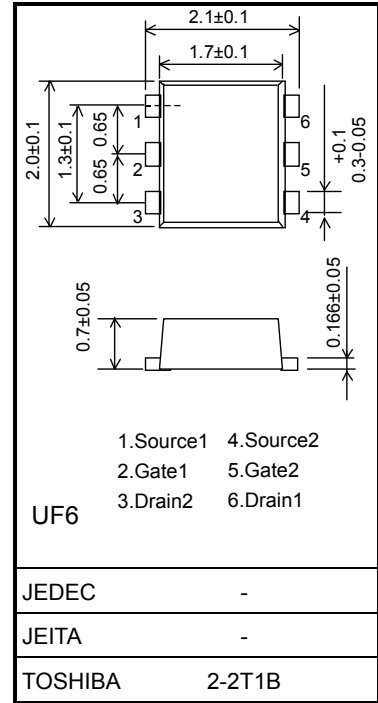
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Total rating

Mounted on an FR4 board  
(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 645 mm<sup>2</sup>)

Unit: mm



Weight: 7.0 mg (typ.)

**Q1 Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit	
Drain-source breakdown voltage	$V_{(BR) DSS}$	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$	20	—	—	V	
	$V_{(BR) DSX}$	$I_D = 1 \text{ mA}, V_{GS} = -10 \text{ V}$	12	—	—		
Drain cutoff current	$I_{DSS}$	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	1	$\mu\text{A}$	
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 1$	$\mu\text{A}$	
Gate threshold voltage	$V_{th}$	$V_{DS} = 3 \text{ V}, I_D = 1 \text{ mA}$	0.35	—	1.0	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 \text{ V}, I_D = 200 \text{ mA}$ (Note2)	420	840	—	mS	
Drain-source ON-resistance	$R_{DS(ON)}$	$I_D = 200 \text{ mA}, V_{GS} = 5.0 \text{ V}$ (Note2)	—	0.46	0.63	$\Omega$	
		$I_D = 200 \text{ mA}, V_{GS} = 4.5 \text{ V}$ (Note2)	—	0.51	0.66		
		$I_D = 200 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note2)	—	0.66	0.85		
		$I_D = 100 \text{ mA}, V_{GS} = 1.8 \text{ V}$ (Note2)	—	0.81	1.14		
		$I_D = 50 \text{ mA}, V_{GS} = 1.5 \text{ V}$ (Note2)	—	0.95	1.52		
Input capacitance	$C_{iss}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	46	—	pF	
Output capacitance	$C_{oss}$		—	10.8	—		
Reverse transfer capacitance	$C_{rss}$		—	7.3	—		
Total Gate Charge	$Q_g$	$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ $V_{GS} = 4.0 \text{ V}$	—	1.23	—	nC	
Gate-Source Charge	$Q_{gs}$		—	0.60	—		
Gate-Drain Charge	$Q_{gd}$		—	0.63	—		
Switching time	Turn-on time	$t_{on}$	$V_{DD} = 10 \text{ V}, I_D = 200 \text{ mA}$	—	30	—	ns
	Turn-off time	$t_{off}$	$V_{GS} = 0 \text{ to } 2.5 \text{ V}, R_G = 50 \Omega$	—	75	—	
Drain-source forward voltage	$V_{DSF}$	$I_D = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$ (Note2)	—	-0.88	-1.2	V	

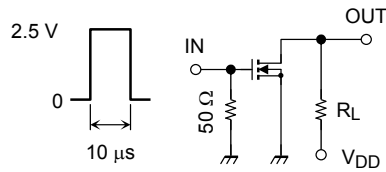
**Q2 Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Conditions	Min	Typ.	Max	Unit	
Drain-source breakdown voltage	$V_{(BR) DSS}$	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	-20	—	—	V	
	$V_{(BR) DSX}$	$I_D = -1 \text{ mA}, V_{GS} = 8 \text{ V}$	-12	—	—		
Drain cutoff current	$I_{DSS}$	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	-10	$\mu\text{A}$	
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 8 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	$\pm 1$	$\mu\text{A}$	
Gate threshold voltage	$V_{th}$	$V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$	-0.3	—	-1.0	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -3 \text{ V}, I_D = -100 \text{ mA}$ (Note2)	190	—	—	mS	
Drain-source ON-resistance	$R_{DS(ON)}$	$I_D = -100 \text{ mA}, V_{GS} = -4.5 \text{ V}$ (Note2)	—	0.95	1.31	$\Omega$	
		$I_D = -80 \text{ mA}, V_{GS} = -2.8 \text{ V}$ (Note2)	—	1.22	1.60		
		$I_D = -40 \text{ mA}, V_{GS} = -1.8 \text{ V}$ (Note2)	—	1.80	2.70		
		$I_D = -30 \text{ mA}, V_{GS} = -1.5 \text{ V}$ (Note2)	—	2.23	3.60		
Input capacitance	$C_{iss}$	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	43	—	pF	
Output capacitance	$C_{oss}$		—	10.3	—		
Reverse transfer capacitance	$C_{rss}$		—	6.1	—		
Total Gate Charge	$Q_g$	$V_{DS} = -10 \text{ V}, I_{DS} = -330 \text{ mA}$ $V_{GS} = -4 \text{ V}$	—	1.2	—	nC	
Gate-Source Charge	$Q_{gs}$		—	0.85	—		
Gate-Drain Charge	$Q_{gd}$		—	0.35	—		
Switching time	Turn-on time	$t_{on}$	$V_{DD} = -10 \text{ V}, I_D = -100 \text{ mA}$	—	90	—	ns
	Turn-off time	$t_{off}$	$V_{GS} = 0 \text{ to } -2.5 \text{ V}, R_G = 50 \Omega$	—	200	—	
Drain-source forward voltage	$V_{DSF}$	$I_D = 330 \text{ mA}, V_{GS} = 0 \text{ V}$ (Note2)	—	0.88	1.2	V	

Note 2: Pulse test

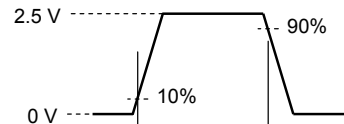
## Q1 Switching Time Test Circuit

(a) Test Circuit

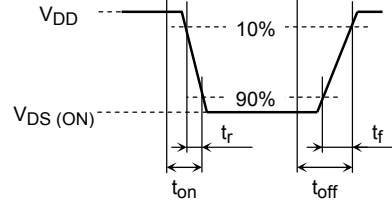


$V_{DD} = 10\text{ V}$   
 D.U.  $\leq 1\%$   
 $V_{IN}$ :  $t_r, t_f < 5\text{ ns}$   
 ( $Z_{out} = 50\ \Omega$ )  
 Common Source  
 $T_a = 25^\circ\text{C}$

(b)  $V_{IN}$

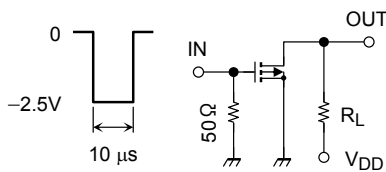


(c)  $V_{OUT}$



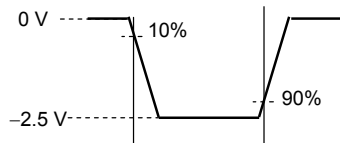
## Q2 Switching Time Test Circuit

(a) Test Circuit

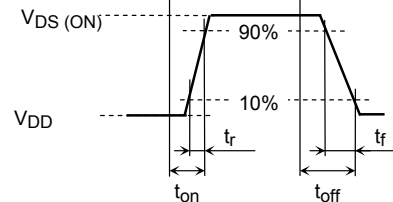


$V_{DD} = -10\text{ V}$   
 D.U.  $\leq 1\%$   
 $V_{IN}$ :  $t_r, t_f < 5\text{ ns}$   
 ( $Z_{out} = 50\ \Omega$ )  
 Common Source  
 $T_a = 25^\circ\text{C}$

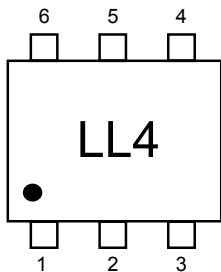
(b)  $V_{IN}$



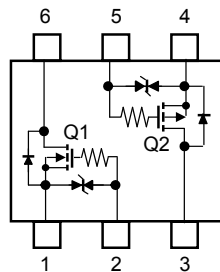
(c)  $V_{OUT}$



## Marking



## Equivalent Circuit (top view)



## Q1 Usage Considerations

Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (1 mA for the Q1 of the SSM6L36TU). Then, for normal switching operation,  $V_{GS(on)}$  must be higher than  $V_{th}$ , and  $V_{GS(off)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(off)} < V_{th} < V_{GS(on)}$ .

Take this into consideration when using the device.

## Q2 Usage considerations

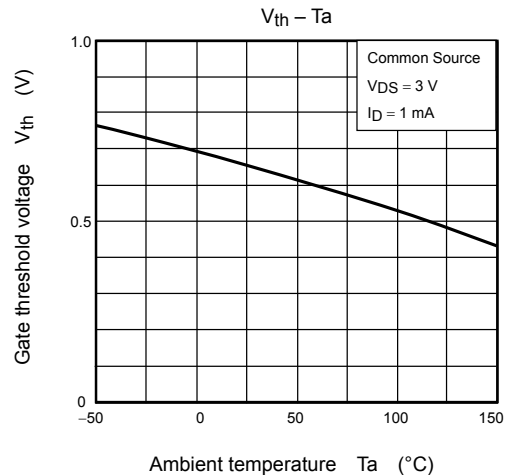
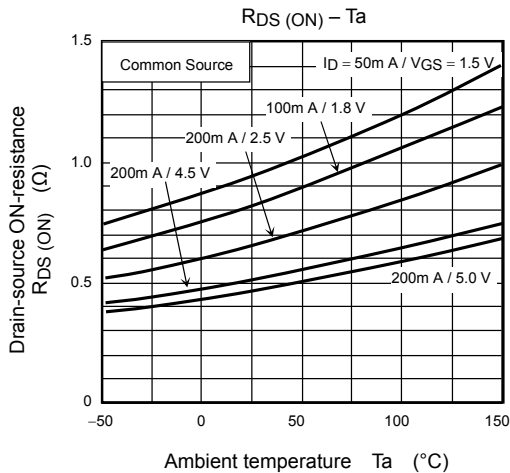
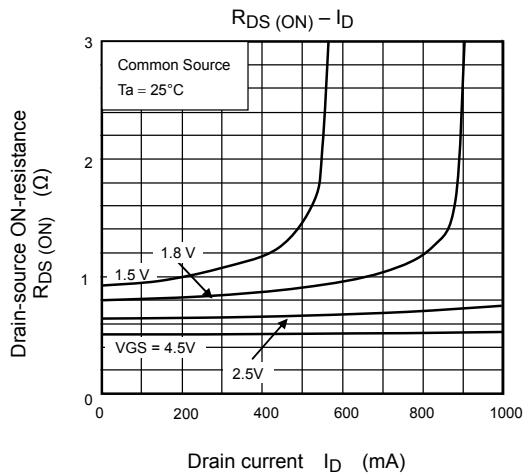
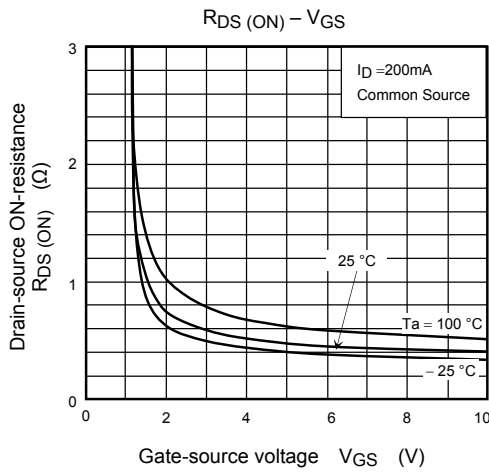
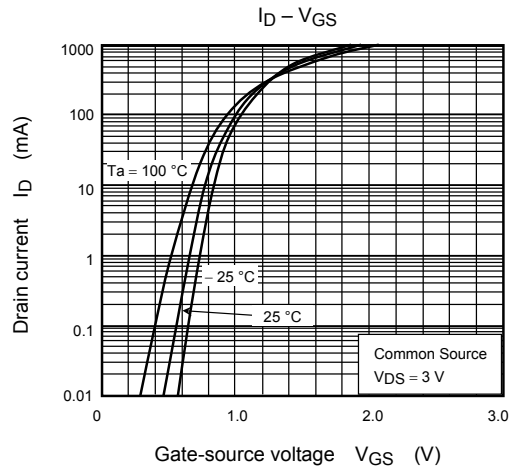
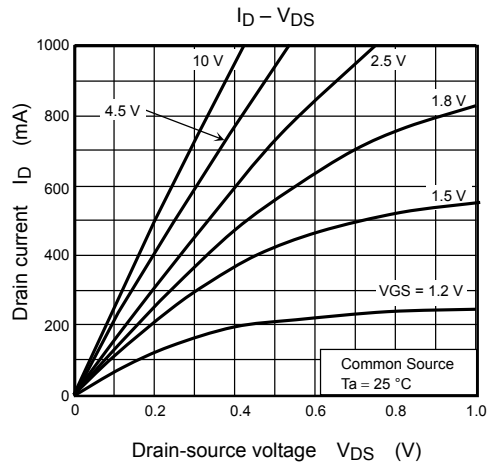
Let  $V_{th}$  be the voltage applied between gate and source that causes the drain current ( $I_D$ ) to below (-1 mA for the Q2 of the SSM6L36TU). Then, for normal switching operation,  $V_{GS(on)}$  must be higher than  $V_{th}$ , and  $V_{GS(off)}$  must be lower than  $V_{th}$ . This relationship can be expressed as:  $V_{GS(off)} < V_{th} < V_{GS(on)}$ .

Take this into consideration when using the device.

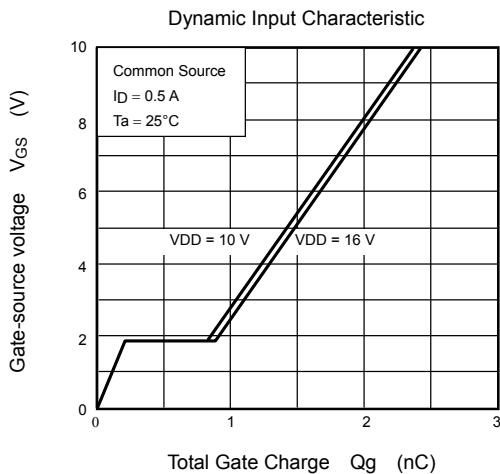
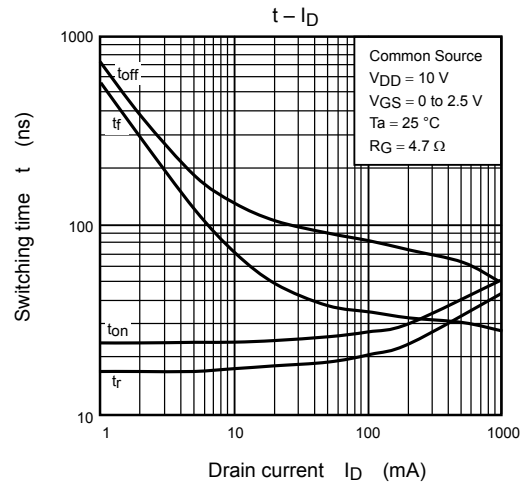
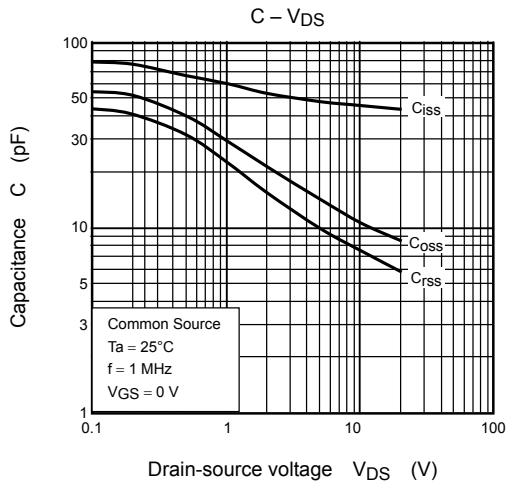
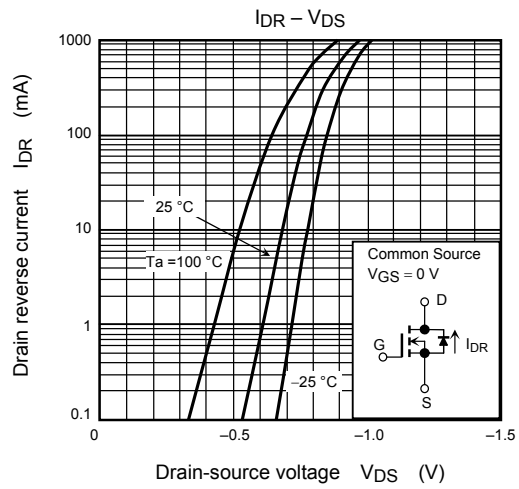
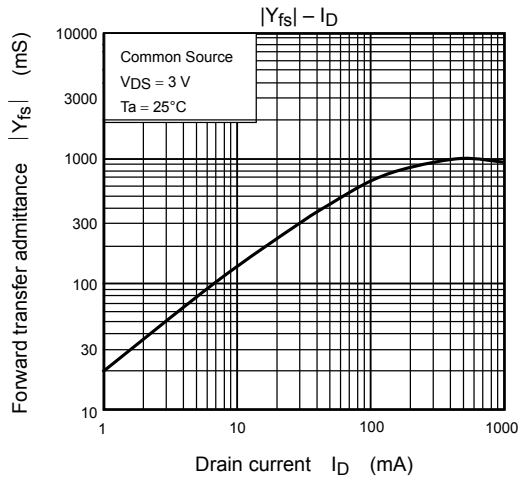
## Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

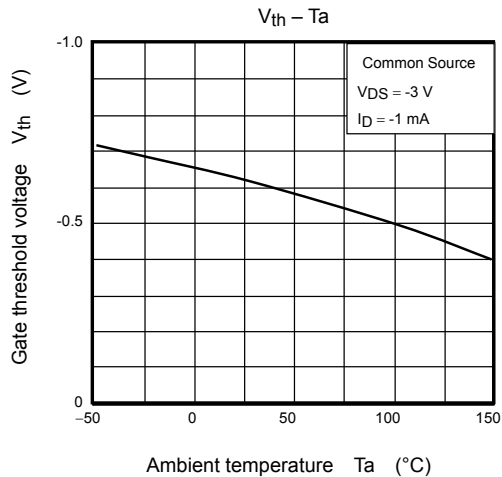
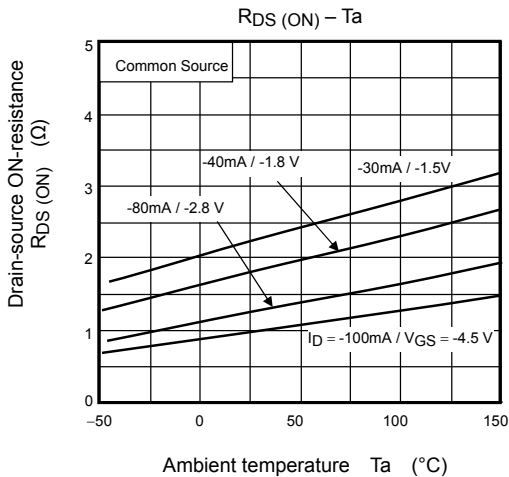
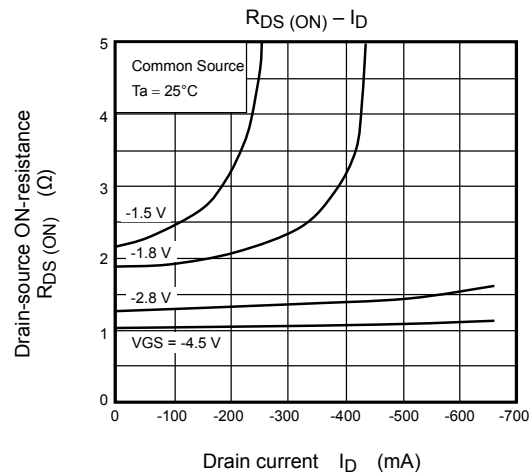
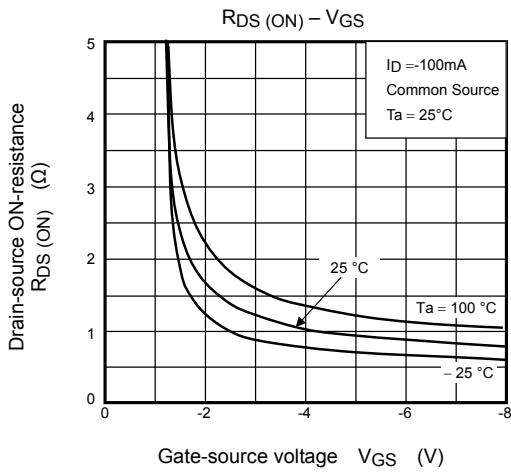
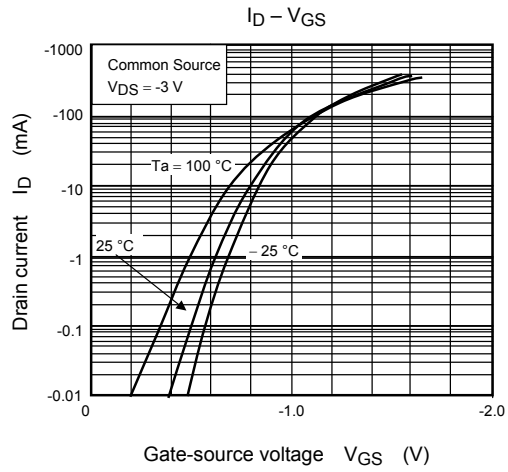
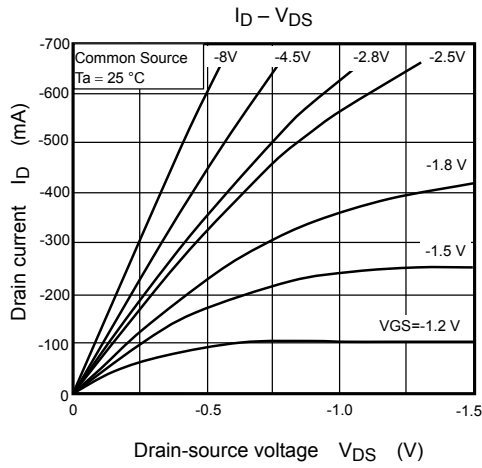
## Q1 (Nch MOS FET)



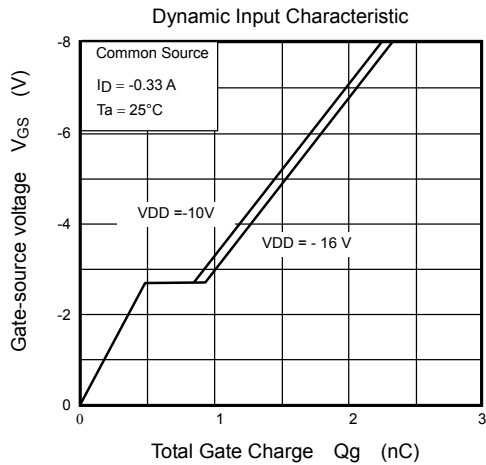
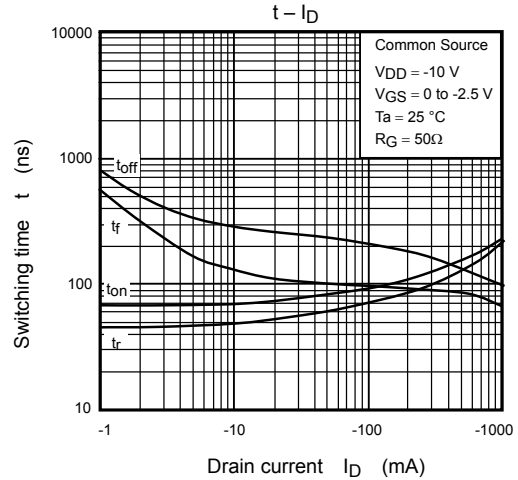
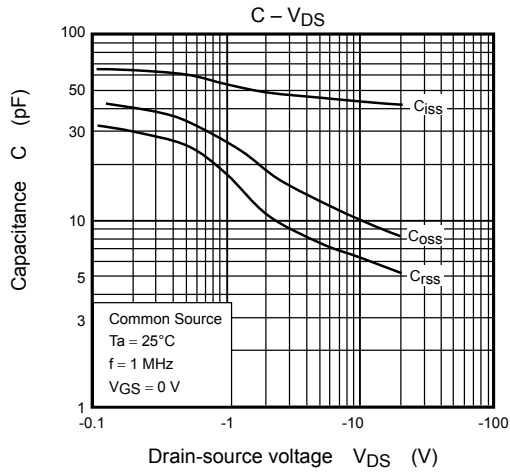
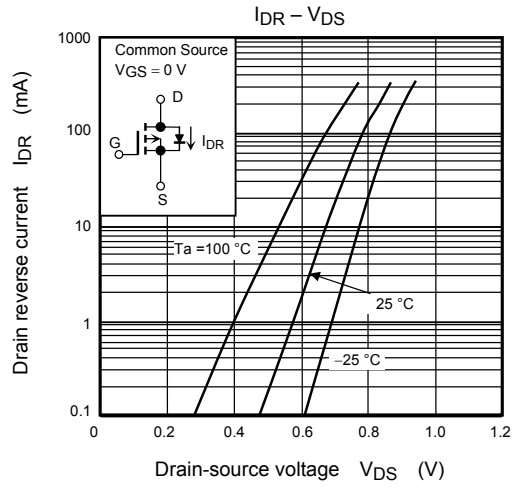
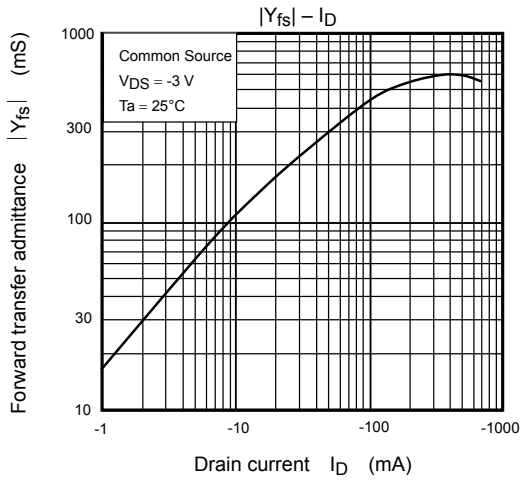
## Q1 (N-ch MOSFET)



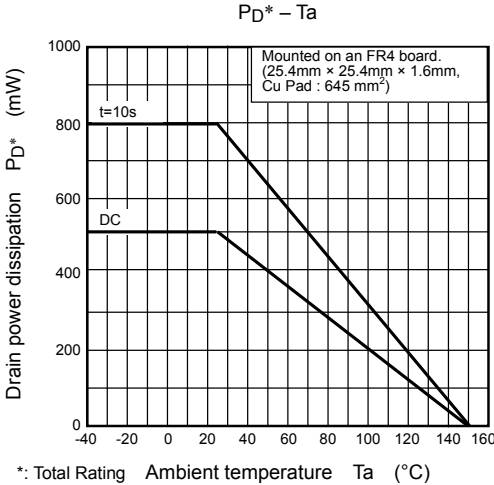
**Q2 (P-ch MOSFET)**



## Q2 (P-ch MOSFET)



Q1, Q2 Common





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20070701-EN GENERAL

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